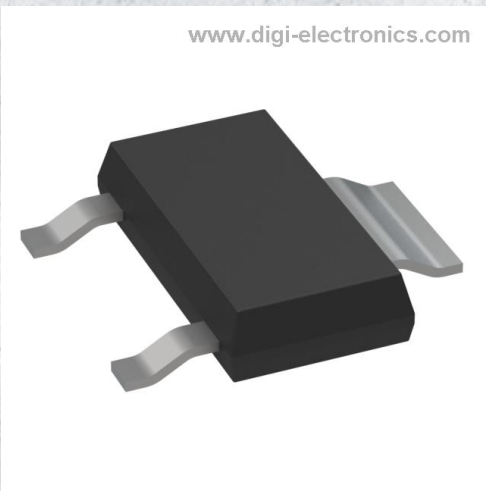
IPN70R1K5CEATMA1 Datasheet



DiGi Electronics Part Number	IPN70R1K5CEATMA1-DG
Manufacturer	Infineon Technologies
Manufacturer Product Number	IPN70R1K5CEATMA1
Description	MOSFET N-CH 700V 5.4A SOT223
Detailed Description	N-Channel 700 V 5.4A (Tc) 5W (Tc) Surface Mount PG-SOT223-3

https://www.DiGi-Electronics.com

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
IPN70R1K5CEATMA1	Infineon Technologies
Series:	Product Status:
CoolMOS™	Active
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
700 V	5.4A (Tc)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
10V	1.5Ohm @ 1A, 10V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
3.5V @ 100µA	10.5 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±20V	225 pF @ 100 V
FET Feature:	Power Dissipation (Max):
-	5W (Tc)
Operating Temperature:	Mounting Type:
-40°C ~ 150°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
PG-SOT223-3	TO-261-4, TO-261AA
Base Product Number:	
IPN70R1	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0095	

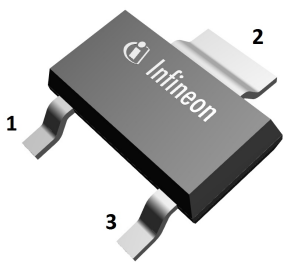
IPN70R1K5CE

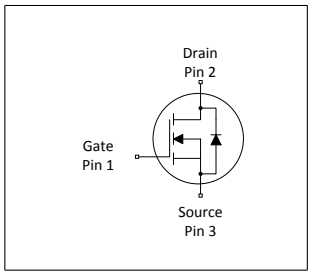
MOSFET

700V CoolMOS™ CE Power Transistor

CoolMOS™ is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies. CoolMOS™ CE is a price-performance optimized platform enabling to target cost sensitive applications in Consumer and Lighting markets by still meeting highest efficiency standards. The new series provides all benefits of a fast switching Superjunction MOSFET while not sacrificing ease of use and offering the best cost down performance ratio available on the market.

PG-SOT223





Features

- Extremely low losses due to very low FOM Rdson*Qg and Eoss
- Very high commutation ruggedness
- Easy to use/drive
- Pb-free plating, Halogen free mold compound
- Qualified for standard grade applications

Applications

Adapter, Charger and Lighting

Please note: For MOSFET paralleling the use of ferrite beads on the gate or seperate totem poles is generally recommended.

Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS} @ $T_{j,max}$	750	V
$R_{DS(on),max}$	1.5	Ω
$Q_{g,typ}$	10.5	nC
$I_{D,pulse}$	8.8	A
E_{oss}@400V	1.2	µJ
Body diode di/dt	500	A/µs

Type / Ordering Code	Package	Marking	Related Links
IPN70R1K5CE	PG-SOT223	70S1K5	see Appendix A

700V CoolMOS™ CE Power Transistor
IPN70R1K5CE

Table of Contents

700V CoolMOS™ CE Power Transistor
IPN70R1K5CE

1 Maximum ratings
at T_j = 25°C, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current[1]	I_D	- -	- -	5.4 3.4	A	T_C = 25°C T_C = 100°C
Pulsed drain current[2]	$I_{D,pulse}$	-	-	8.8	A	T_C = 25°C
Avalanche energy, single pulse	E_{AS}	-	-	26	mJ	I_D = 0.6A; V_{DD} = 50V
Avalanche energy, repetitive	E_{AR}	-	-	0.10	mJ	I_D = 0.6A; V_{DD} = 50V
Avalanche current, repetitive	I_{AR}	-	-	0.6	A	-
MOSFET dv/dt ruggedness	dv/dt	-	-	50	V/ns	V_{DS} = 0...480V
Gate source voltage	V_{GS}	-20 -30	- -	20 30	V	static; AC (f>1 Hz)
Power dissipation	P_{tot}	-	-	5.0	W	T_C = 25°C
Operating and storage temperature	T_j, T_{stg}	-40	-	150	°C	-
Continuous diode forward current	I_S	-	-	1.2	A	T_C = 25°C
Diode pulse current[2]	$I_{S,pulse}$	-	-	8.8	A	T_C = 25°C
Reverse diode dv/dt[3]	dv/dt	-	-	15	V/ns	V_{DS} = 0...400V, I_{SD}<=I_S, T_j=25°C
Maximum diode commutation speed[3]	di_f/dt	-	-	500	A/µs	V_{DS} = 0...400V, I_{SD}<=I_S, T_j=25°C

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - solder point	R_{thJS}	-	-	23.8	°C/W	-
Thermal resistance, junction - ambient for minimal footprint	R_{thJA}	-	-	160	°C/W	minimal footprint
Thermal resistance, junction - ambient soldered on copper area	R_{thJA}	-	-	75	°C/W	Device on 40mm*40mm*1.5 epoxy PCB FR4 with 6cm² (one layer 70µm thick) copper area for drain connection and cooling. PCB is vertical without blown air.
Soldering temperature, wavesoldering only allowed at leads	T_{sold}	-	-	260	°C	reflow MSL3

[1] DPAK equivalent. Limited by $T_{j\,max}$. Maximum duty cycle D=0.5
[2] Pulse width t_p limited by $T_{j,max}$
[3] V_{DClink}=400V; $V_{DS,peak}$<$V_{(BR)DSS}$; identical low side and high side switch with identical R_G

3 Electrical characteristics

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	700	-	-	V	V_{GS}=0V, I_D=1mA
Gate threshold voltage	$V_{GS(th)}$	2.50	3	3.50	V	V_{DS}=V_{GS}, I_D=0.1mA
Zero gate voltage drain current	I_{DSS}	- -	- 10	1 -	µA	V_{DS}=700V, V_{GS}=0V, T_j=25°C V_{DS}=700V, V_{GS}=0V, T_j=150°C
Gate-source leakage curent	I_{GSS}	-	-	100	nA	V_{GS}=20V, V_{DS}=0V
Drain-source on-state resistance	$R_{DS(on)}$	- -	1.35 3.51	1.50 -	Ω	V_{GS}=10V, I_D=1A, T_j=25°C V_{GS}=10V, I_D=1A, T_j=150°C
Gate resistance	R_G	-	6.5	-	Ω	f=1 MHz, open drain

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	225	-	pF	V_{GS}=0V, V_{DS}=100V, f=1MHz
Output capacitance	C_{oss}	-	18	-	pF	V_{GS}=0V, V_{DS}=100V, f=1MHz
Effective output capacitance, energy related[1)]	$C_{o(er)}$	-	10	-	pF	V_{GS}=0V, V_{DS}=0...480V
Effective output capacitance, time related[2)]	$C_{o(tr)}$	-	42	-	pF	I_D=constant, V_{GS}=0V, V_{DS}=0...480V
Turn-on delay time	$t_{d(on)}$	-	7.7	-	ns	V_{DD}=400V, V_{GS}=13V, I_D=1.5A, R_G=10.2Ω
Rise time	t_r	-	5.9	-	ns	V_{DD}=400V, V_{GS}=13V, I_D=1.5A, R_G=10.2Ω
Turn-off delay time	$t_{d(off)}$	-	33	-	ns	V_{DD}=400V, V_{GS}=13V, I_D=1.5A, R_G=10.2Ω
Fall time	t_f	-	18.2	-	ns	V_{DD}=400V, V_{GS}=13V, I_D=1.5A, R_G=10.2Ω

Table 6 Gate charge characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	1.3	-	nC	V_{DD}=480V, I_D=1.5A, V_{GS}=0 to 10V
Gate to drain charge	Q_{gd}	-	5.8	-	nC	V_{DD}=480V, I_D=1.5A, V_{GS}=0 to 10V
Gate charge total	Q_g	-	10.5	-	nC	V_{DD}=480V, I_D=1.5A, V_{GS}=0 to 10V
Gate plateau voltage	$V_{plateau}$	-	5.4	-	V	V_{DD}=480V, I_D=1.5A, V_{GS}=0 to 10V

[1)] $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 480V
[2)] $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 480V

700V CoolMOS™ CE Power Transistor
IPN70R1K5CE

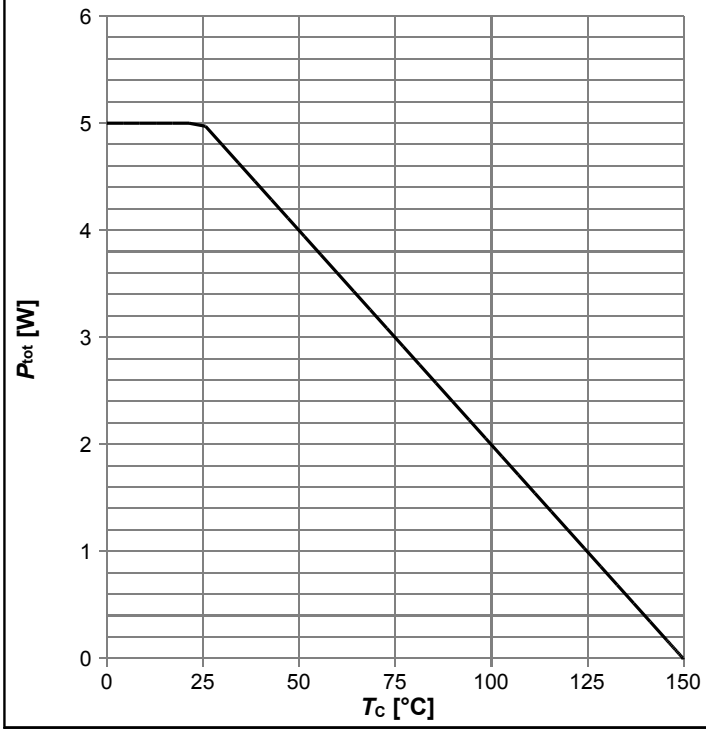
Table 7 Reverse diode characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	V_{SD}	-	0.9	-	V	V_{GS}=0V, I_F=1.5A, T_f=25°C
Reverse recovery time	t_{rr}	-	200	-	ns	V_R=400V, I_F=1.5A, di_F/dt=100A/µs
Reverse recovery charge	Q_{rr}	-	0.9	-	µC	V_R=400V, I_F=1.5A, di_F/dt=100A/µs
Peak reverse recovery current	I_{rrm}	-	8	-	A	V_R=400V, I_F=1.5A, di_F/dt=100A/µs

700V CoolMOS™ CE Power Transistor
IPN70R1K5CE

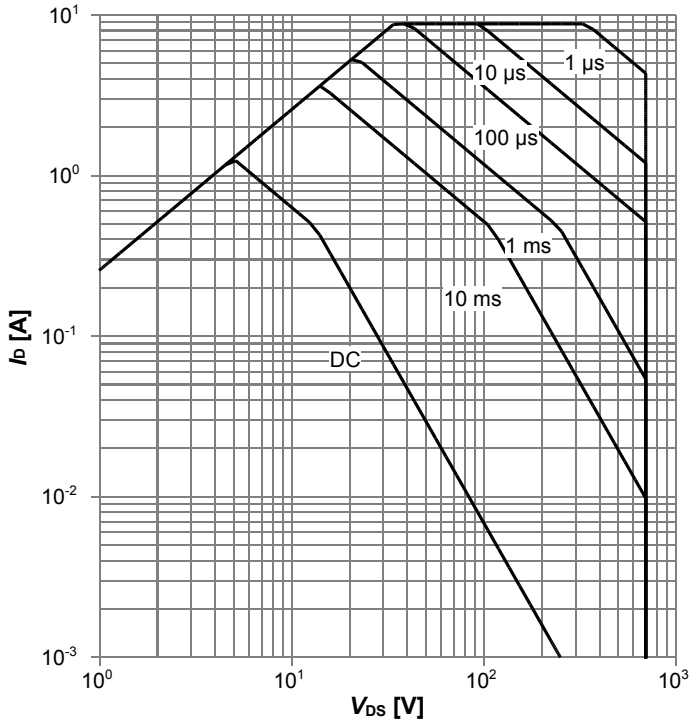
4 Electrical characteristics diagrams

Diagram 1: Power dissipation



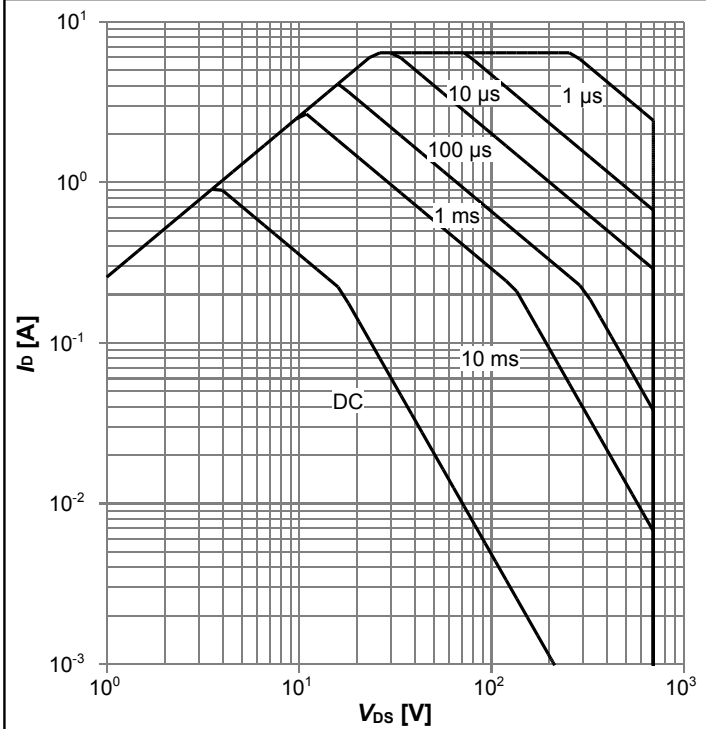
P_{tot}=f(T_C)

Diagram 2: Safe operating area



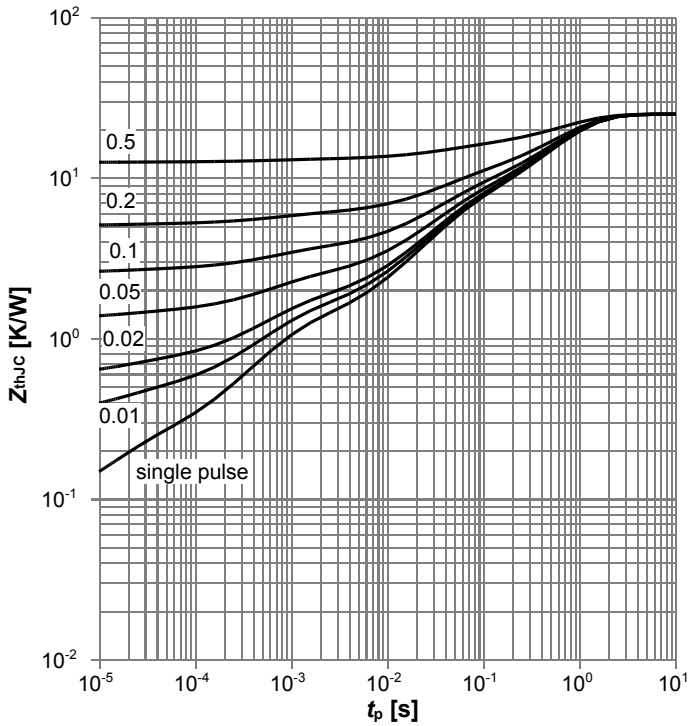
I_D=f(V_{DS}); T_C=25 °C; D=0; parameter: t_p

Diagram 3: Safe operating area



I_D=f(V_{DS}); T_C=80 °C; D=0; parameter: t_p

Diagram 4: Max. transient thermal impedance



Z_{thJC} =f(t_P); parameter: D=t_p/T

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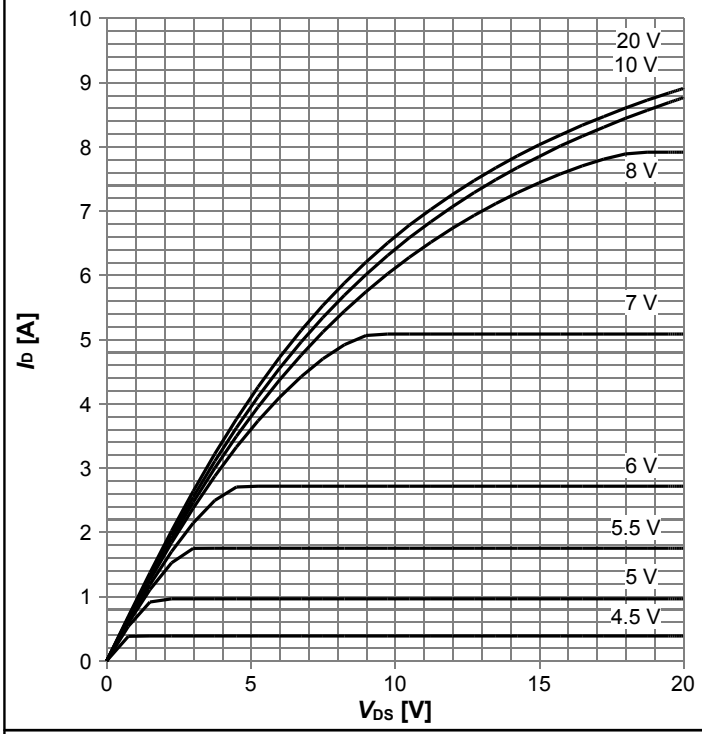
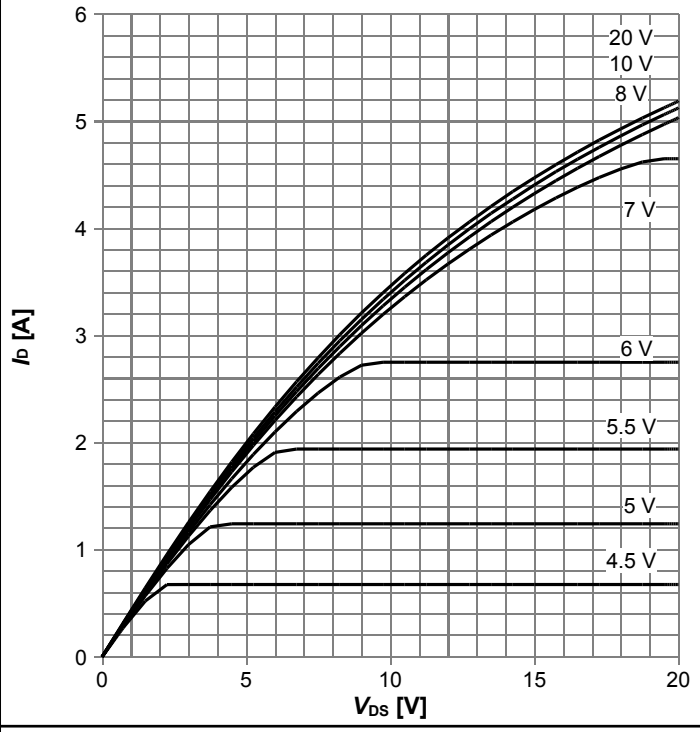
Diagram 5: Typ. output characteristics



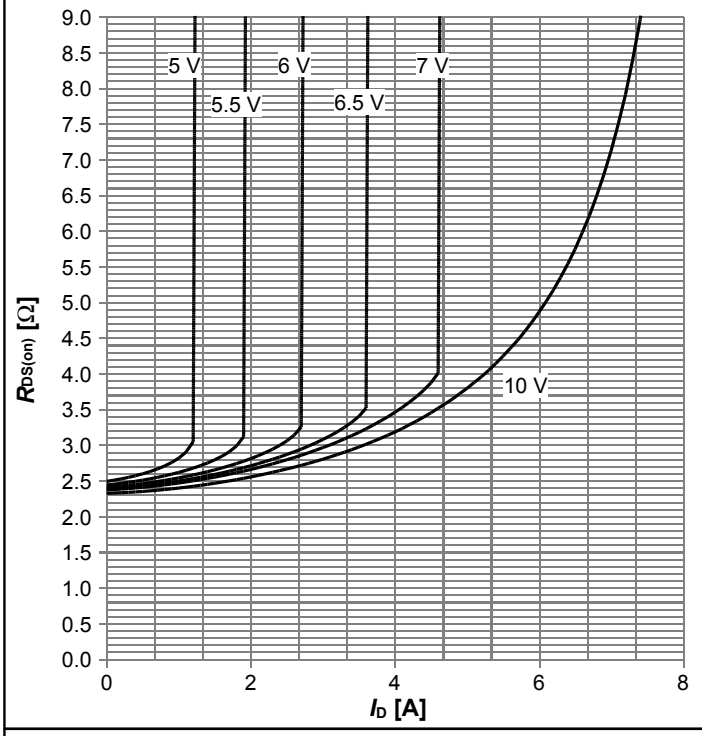
$I_D=f(V_{DS})$; $T_j=25$ °C; parameter: V_{GS}

Diagram 6: Typ. output characteristics



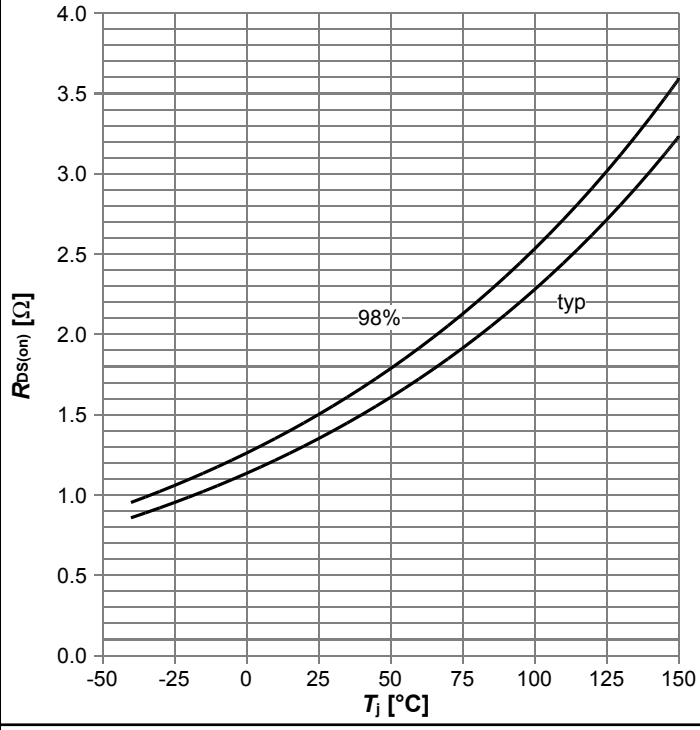
$I_D=f(V_{DS})$; $T_j=125$ °C; parameter: V_{GS}

Diagram 7: Typ. drain-source on-state resistance



$R_{DS(on)}=f(I_D)$; $T_j=125$ °C; parameter: V_{GS}

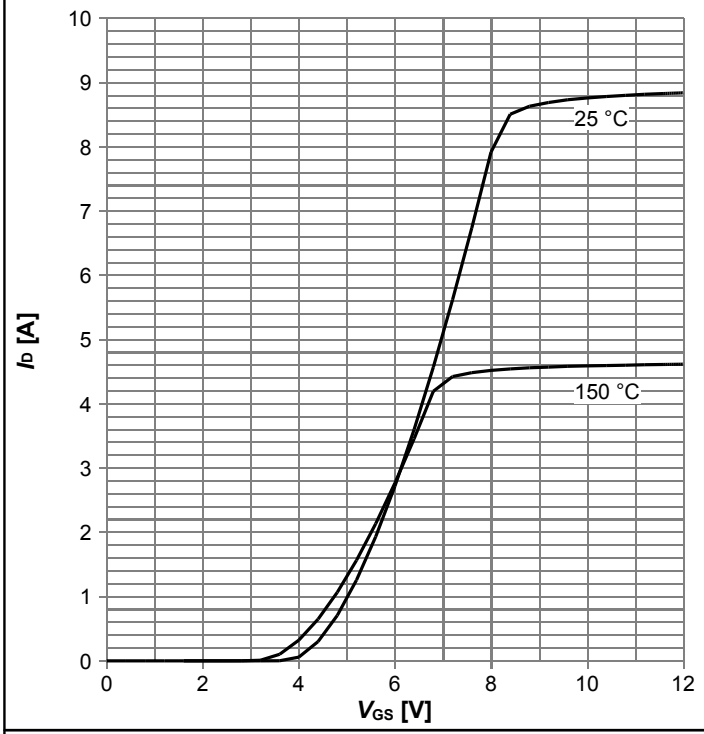
Diagram 8: Drain-source on-state resistance



$R_{DS(on)}=f(T_j)$; $I_D=1.0$ A; $V_{GS}=10$ V

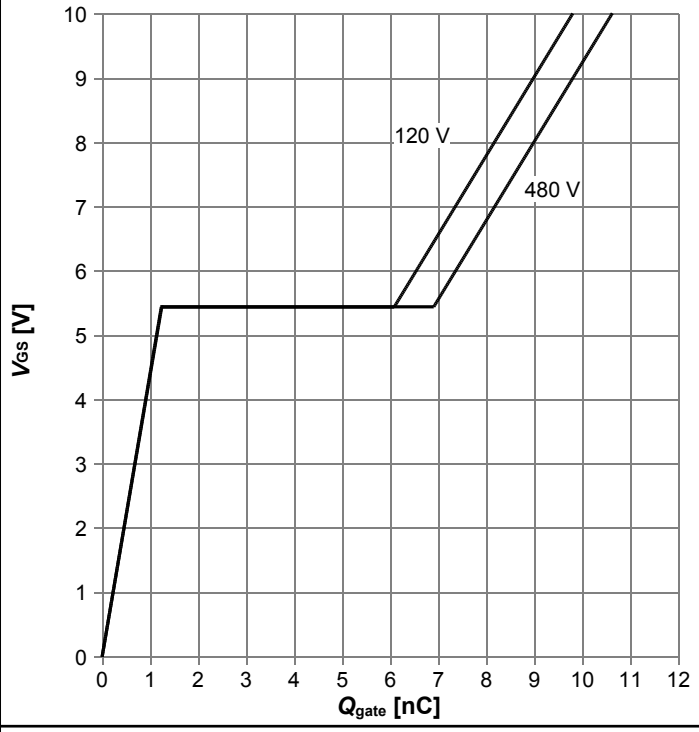
700V CoolMOS™ CE Power Transistor
IPN70R1K5CE

Diagram 9: Typ. transfer characteristics



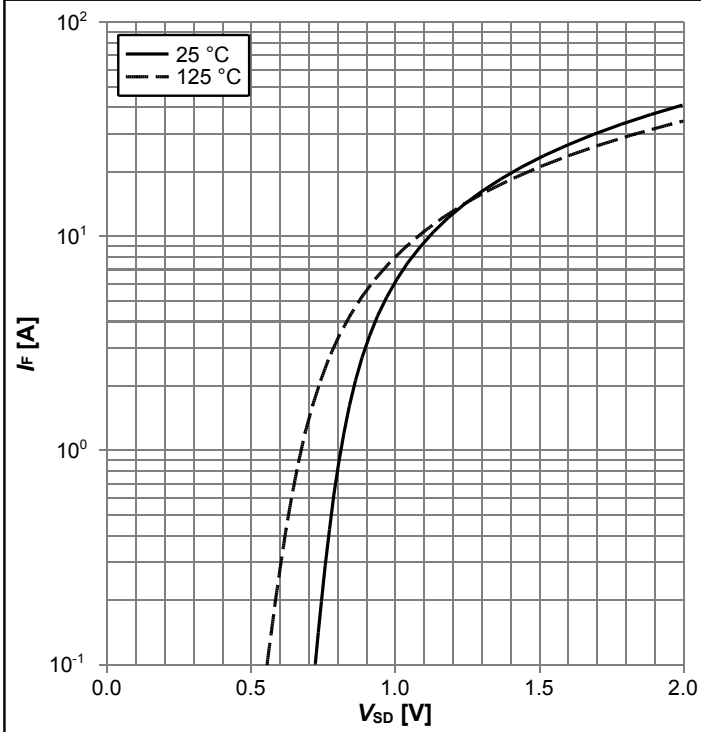
I_D=f(V_{GS}); V_{DS}=20V; parameter: T_j

Diagram 10: Typ. gate charge



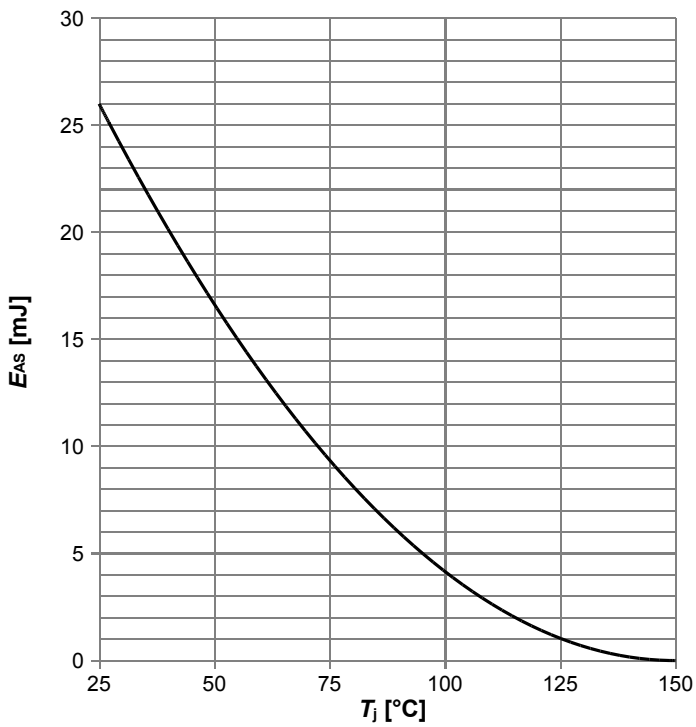
V_{GS}=f(Q_{gate}); I_D=1.5 A pulsed; parameter: V_{DD}

Diagram 11: Forward characteristics of reverse diode



I_F=f(V_{SD}); parameter: T_j

Diagram 12: Avalanche energy



E_{AS}=f(T_j); I_D=0.6 A; V_{DD}=50 V

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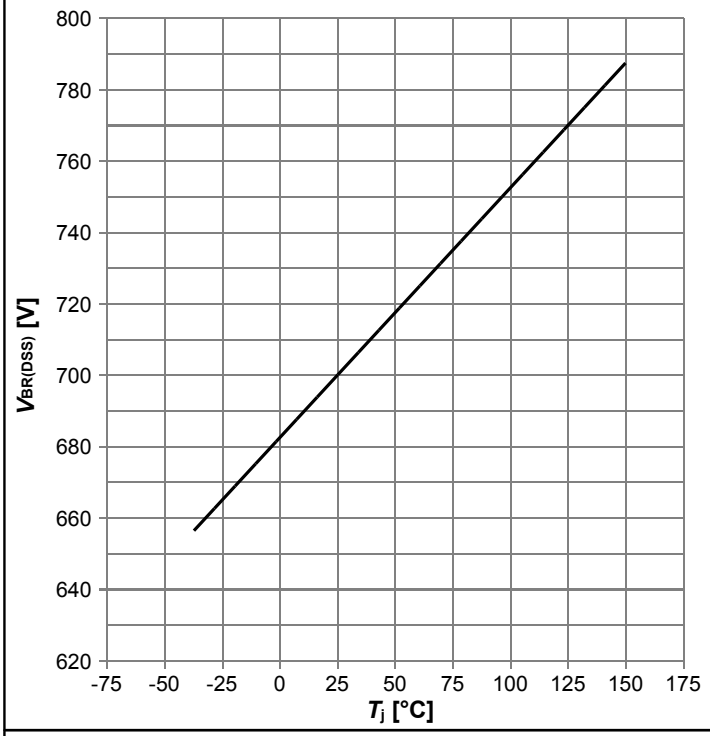
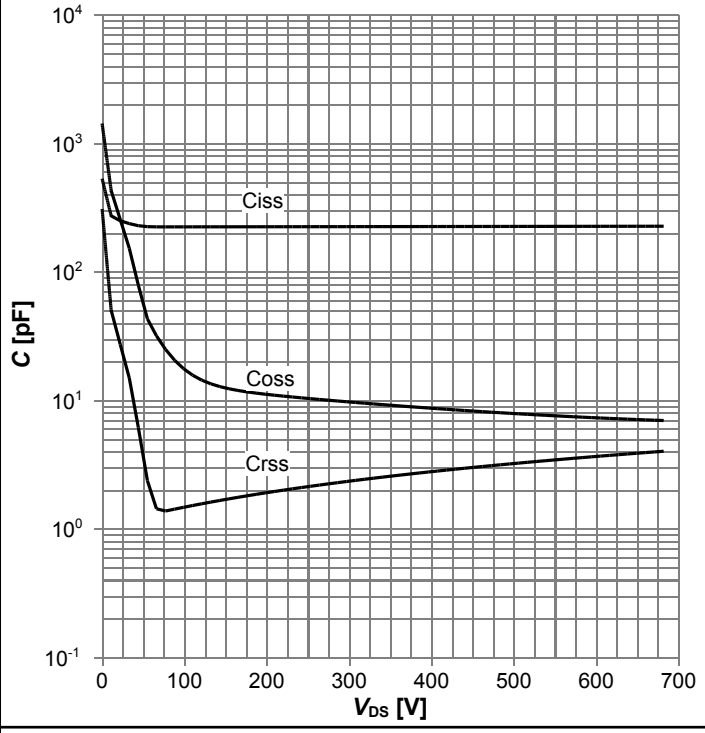
Diagram 13: Drain-source breakdown voltage



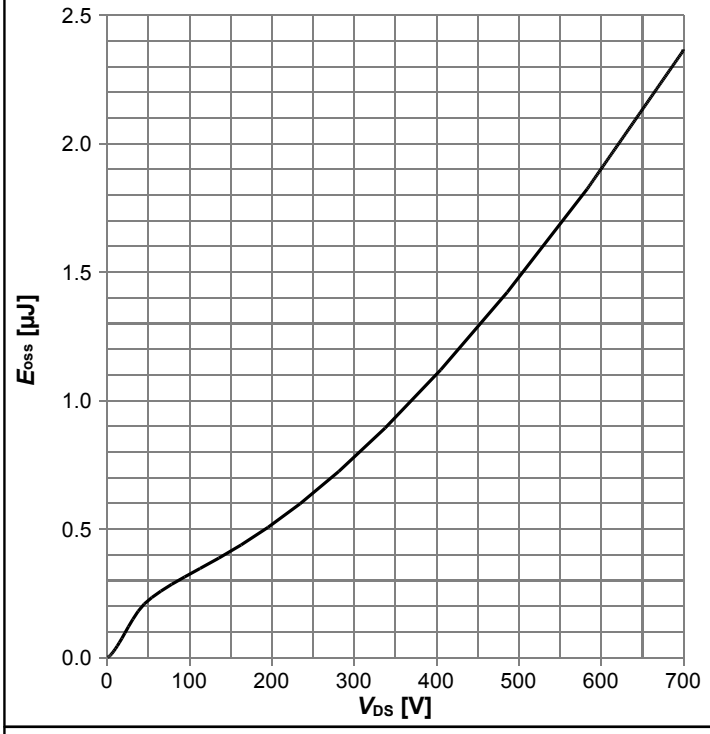
$V_{BR(DSS)}$=f(T_j); I_D=1 mA

Diagram 14: Typ. capacitances



C=f(V_{DS}); V_{GS}=0 V; f=1 MHz

Diagram 15: Typ. Coss stored energy



E_{oss}=f(V_{DS})

5 Test Circuits

Table 8 Diode characteristics

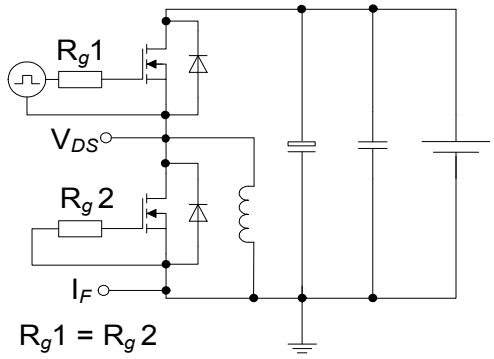
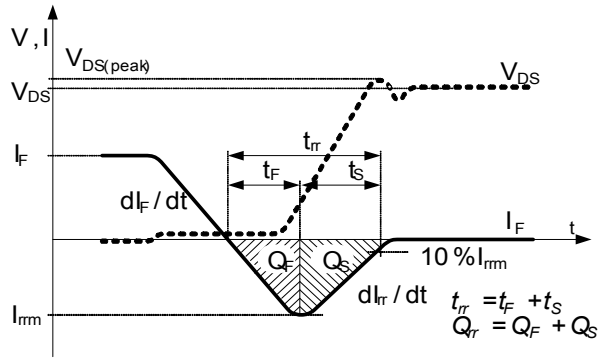
Test circuit for diode characteristics	Diode recovery waveform
	

Table 9 Switching times

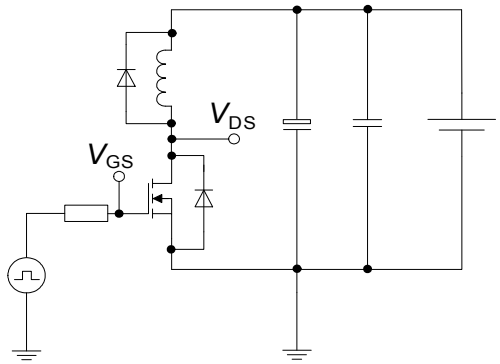
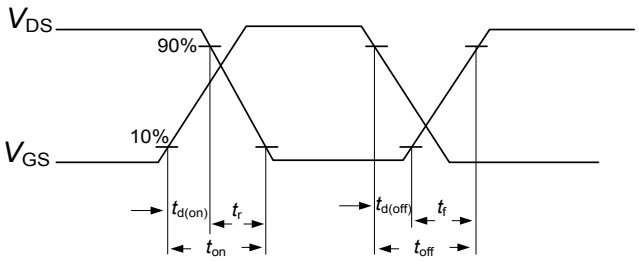
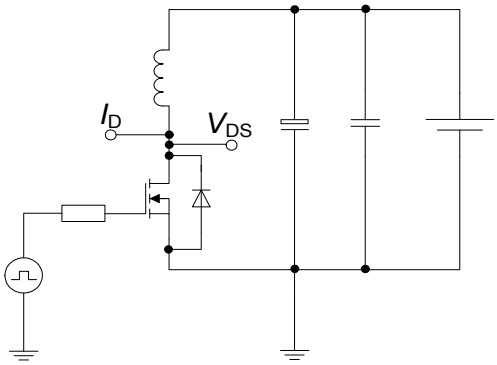
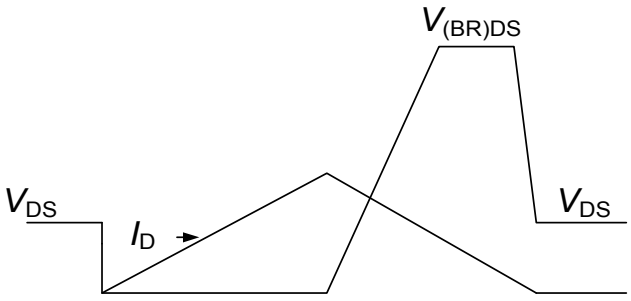
Switching times test circuit for inductive load	Switching times waveform
	

Table 10 Unclamped inductive load

Unclamped inductive load test circuit	Unclamped inductive waveform
	

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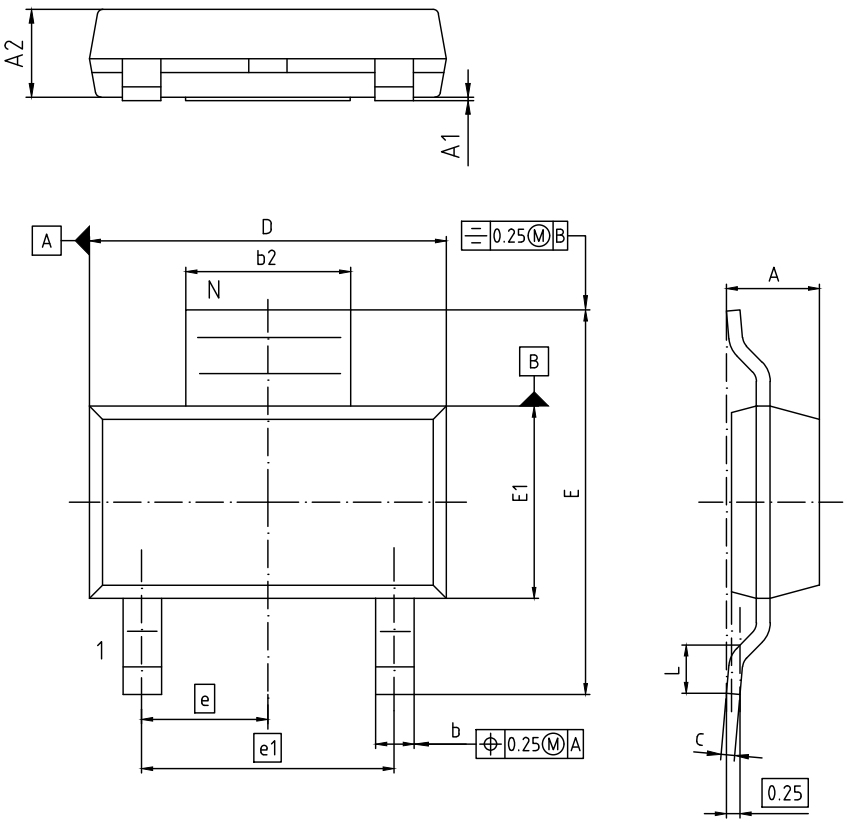
6 Package Outlines



NOTES:

1. ALL DIMENSIONS REFER TO JEDEC STANDARD TO-261

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.52	1.80	0.060	0.071
A1	-	0.10	-	0.004
A2	1,50	1.70	0.059	0.067
b	0.60	0.80	0.024	0.031
b2	2.95	3.10	0.116	0.122
c	0.24	0.32	0.009	0.013
D	6.30	6.70	0.248	0.264
E	6.70	7.30	0.264	0.287
E1	3.30	3.70	0.130	0.146
e	2.3 BASIC		0.091 BASIC	
e1	4.6 BASIC		0.181 BASIC	
L	0.75	1.10	0.030	0.043
N	3		3	
O	0°	10°	0°	10°

DOCUMENT NO.
Z8B00180553

SCALE
0 2.5 5mm

EUROPEAN PROJECTION

ISSUE DATE
24-02-2016

REVISION
01

Figure 1 Outline PG-SOT223, dimensions in mm/inches

7 Appendix A

Table 11 Related Links

- **IFX CoolMOS Webpage:** www.infineon.com
- **IFX Design tools:** www.infineon.com

700V CoolMOS™ CE Power Transistor
IPN70R1K5CE

Revision History

IPN70R1K5CE

Revision: 2016-04-29, Rev. 2.0

Previous Revision		
Revision	Date	Subjects (major changes since last revision)
2.0	2016-04-29	Release of final version

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